

PBSS306PZ

100 V, 4.1 A PNP low VCEsat (BISS) transistor Rev. 3 — 26 July 2011

Product data sheet

1. **Product profile**

1.1 General description

PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a SOT223 (SC-73) small Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS306NZ.

1.2 Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FF}) at high I_C
- High efficiency due to less heat generation
- Smaller Printed-Circuit Board (PCB) area than for conventional transistors
- AEC-Q101 qualified

1.3 Applications

- High-voltage DC-to-DC conversion
- High-voltage MOSFET gate driving
- High-voltage motor control
- High-voltage power switches (e.g. motors, fans)
- Automotive applications

1.4 Quick reference data

Table 1. **Quick reference data**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-100	V
I _C	collector current		-	-	-4.1	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	-8.2	Α
R _{CEsat}	collector-emitter saturation resistance	I_{C} = -4 A; I_{B} = -400 mA; pulsed; $t_{p} \le 300 \mu\text{s}; \ \delta \le 0.02 ; \ T_{amb} = 25 ^{\circ}\text{C}$	-	56	80	mΩ



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2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		2.4
2	С	collector	4	2, 4
3	Е	emitter		1 —
4	С	collector		3
			SOT223 (SC-73)	sym028

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBSS306PZ	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223

4. Marking

Table 4. Marking codes

Type number	Marking code
PBSS306PZ	S306PZ

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	-100	V
V _{CEO}	collector-emitter voltage	open base		-	-100	V
V_{EBO}	emitter-base voltage	open collector		-	-5	V
I _C	collector current			-	-4.1	Α
I _{CM}	peak collector current	single pulse; $t_p \le 1$ ms		-	-8.2	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.7	W
			[2]	-	1.7	W
			[3]	-	2	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

PBSS306PZ

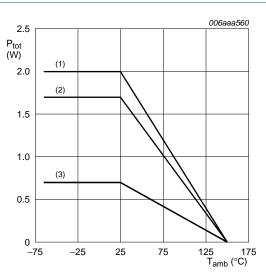
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^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

^[3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

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- (1) Ceramic PCB, Al₂O₃, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm²
- (3) FR4 PCB, standard footprint

Fig 1. Power derating curves

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance	[2	<u>[1]</u>	-	-	179	K/W
	from junction to ambient		[2]	-	-	74	K/W
	ambient		[3]	-	-	63	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	15	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

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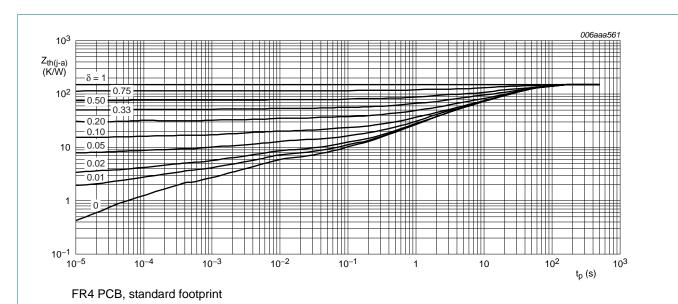


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

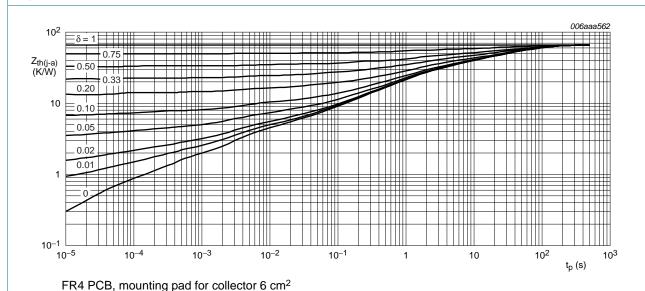
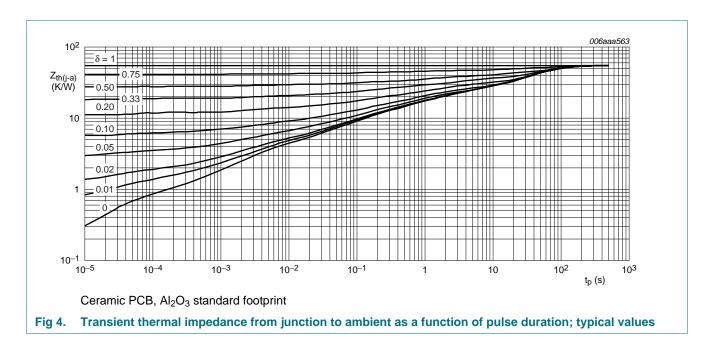


Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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7. Characteristics

Table 7. Characteristics

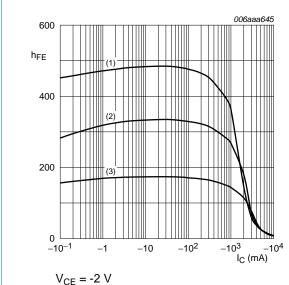
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	$V_{CB} = -80 \text{ V}; I_{E} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nΑ
	current	$V_{CB} = -80 \text{ V}; I_E = 0 \text{ A}; T_j = 150 \text{ °C};$ $T_{amb} = 25 \text{ °C}$	-	-	-50	μΑ
I _{CES}	collector-emitter cut-off current	$V_{CE} = -48 \text{ V}; V_{BE} = 0 \text{ V}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -2 V; I_{C} = -0.5 A; pulsed; $t_{p} \le 300 \text{ µs}; \delta \le 0.02 ; T_{amb} = 25 \text{ °C}$	200	300	-	
		V_{CE} = -2 V; I_{C} = -1 A; pulsed; $t_{p} \le 300 \text{ µs}; \delta \le 0.02 ; T_{amb} = 25 \text{ °C}$	150	260	-	
		V_{CE} = -2 V; I_{C} = -2 A; pulsed; $t_{p} \le 300 \text{ µs}; \delta \le 0.02 ; T_{amb} = 25 \text{ °C}$	100	175	-	
		V_{CE} = -2 V; I_{C} = -4 A; pulsed; $t_{p} \le 300 \text{ µs}; \delta \le 0.02 ; T_{amb} = 25 \text{ °C}$	25	40	-	
V _{CEsat}	collector-emitter saturation voltage	I_{C} = -0.5 A; I_{B} = -50 mA; pulsed; $t_{p} \le 300 \text{ µs; } \delta \le 0.02 \text{ ; } T_{amb} = 25 \text{ °C}$	-	-45	-65	mV
		I_C = -1 A; I_B = -50 mA; pulsed; $t_p \le 300$ μs; $\delta \le 0.02$; T_{amb} = 25 °C	-	-90	-130	mV
		$I_C = -4 \text{ A}$; $I_B = -400 \text{ mA}$; pulsed; $t_p \le 300 \text{ µs}$; $\delta \le 0.02$; $T_{amb} = 25 \text{ °C}$	-	-225	-320	mV
		I_{C} = -4.1 A; I_{B} = -410 mA; pulsed; $t_{p} \le 300 \text{ µs}; \delta \le 0.02 ; T_{amb} = 25 \text{ °C}$	-	-230	-325	mV
R _{CEsat}	collector-emitter saturation resistance	I_C = -4 A; I_B = -400 mA; pulsed; $t_p \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb} = 25 \ ^{\circ}C$	-	56	80	mΩ
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Table 7. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{BEsat} base-emitter saturation voltage	base-emitter saturation voltage	I_C = -1 A; I_B = -100 mA; pulsed; $t_p \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	-	-0.81	-0.9	V
	I_{C} = -4 A; I_{B} = -400 mA; pulsed; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	-	-0.93	-1.05	V	
V_{BEon}	base-emitter turn-on voltage	V_{CE} = -2 V; I_{C} = -2 A; pulsed; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	-	-0.78	-0.85	V
t _d	delay time	V_{CC} = -12.5 V; I_{C} = -3 A; I_{Bon} = -0.15 A; I_{Boff} = 0.15 A; T_{amb} = 25 °C	-	15	-	ns
t _r	rise time		-	185	-	ns
t _{on}	turn-on time		-	200	-	ns
ts	storage time		-	150	-	ns
t _f	fall time		-	175	-	ns
t _{off}	turn-off time		-	325	-	ns
f _T	transition frequency	$V_{CE} = -10 \text{ V}; I_{C} = -100 \text{ mA};$ f = 100 MHz; $T_{amb} = 25 ^{\circ}\text{C}$	-	100	-	MHz
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$ f = 1 MHz; $T_{amb} = 25 \text{ °C}$	-	50	80	pF



(1) $T_{amb} = 100 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 5. DC current gain as a function of collector current; typical values

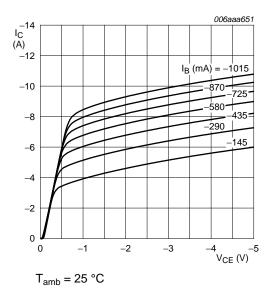
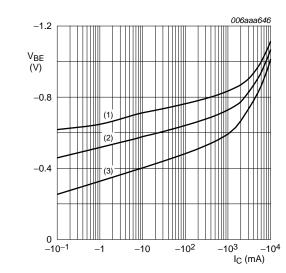


Fig 6. Collector current as a function of collector-emitter voltage; typical values

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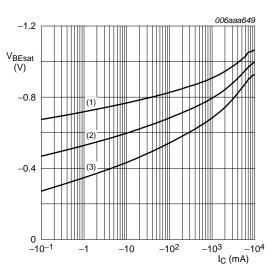


$$V_{CE} = -2 V$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 7. Base-emitter voltage as a function of collector current; typical values



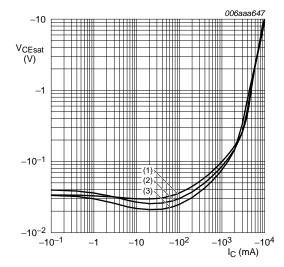
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 8. Base-emitter saturation voltage as a function of collector current; typical values



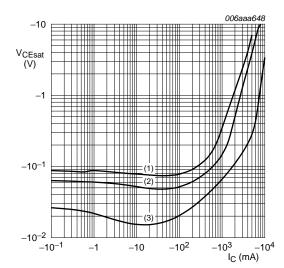
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 9. Collector-emitter saturation voltage as a function of collector current; typical values



$$T_{amb} = 25 \, ^{\circ}C$$

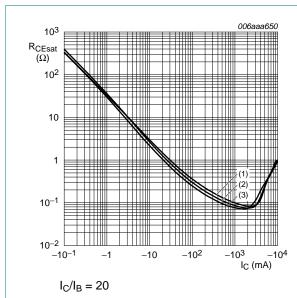
(1)
$$I_C/I_B = 100$$

(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 10$$

Fig 10. Collector-emitter saturation voltage as a function of collector current; typical values

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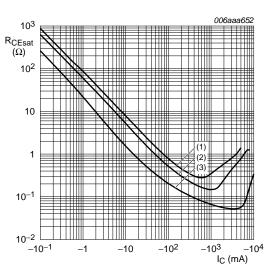


(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 11. Collector-emitter saturation resistance as a function of collector current; typical values



$$T_{amb} = 25$$
 °C

(1)
$$I_C/I_B = 100$$

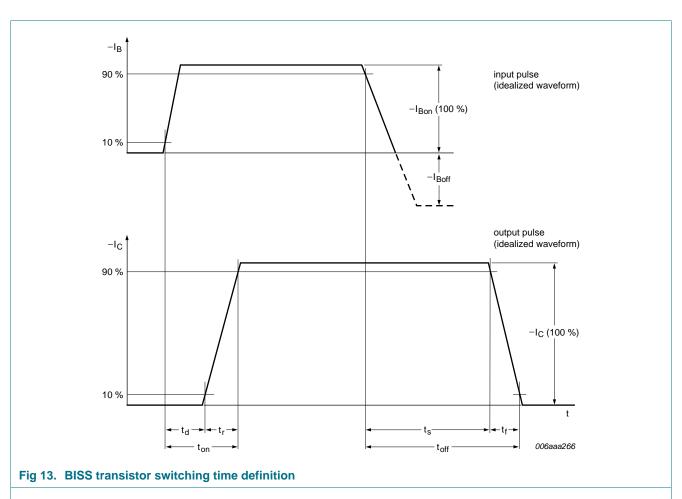
(2)
$$I_C/I_B = 50$$

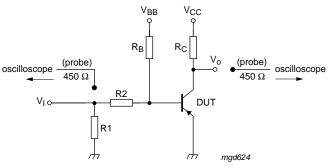
(3)
$$I_C/I_B = 10$$

Fig 12. Collector-emitter saturation resistance as a function of collector current; typical values

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8. Test information





 V_{CC} = -12.5 V; I_{C} = -3 A; I_{Bon} = -0.15 A; I_{Boff} = 0.15 A

Fig 14. Test circuit for switching times

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors and is suitable for use in automotive applications.

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9. Package outline

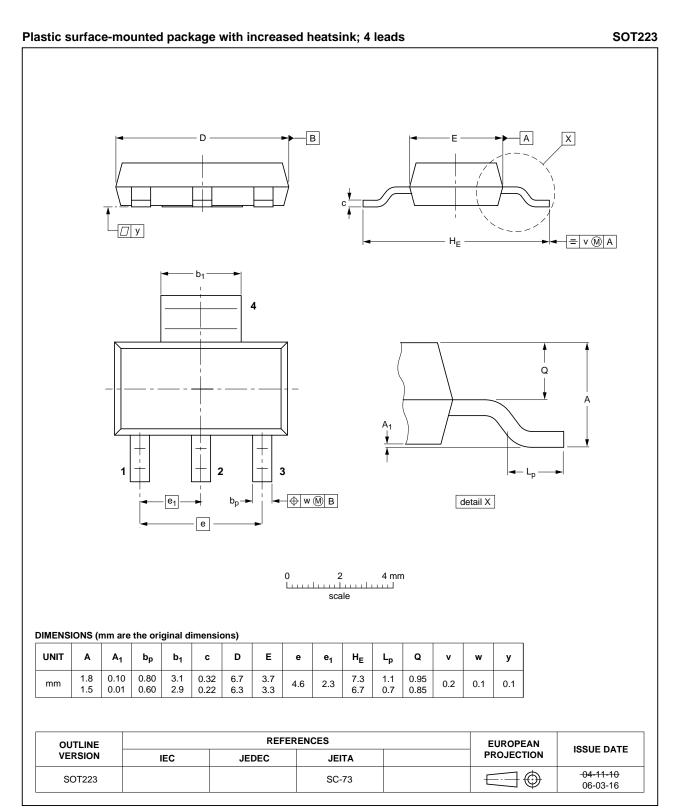
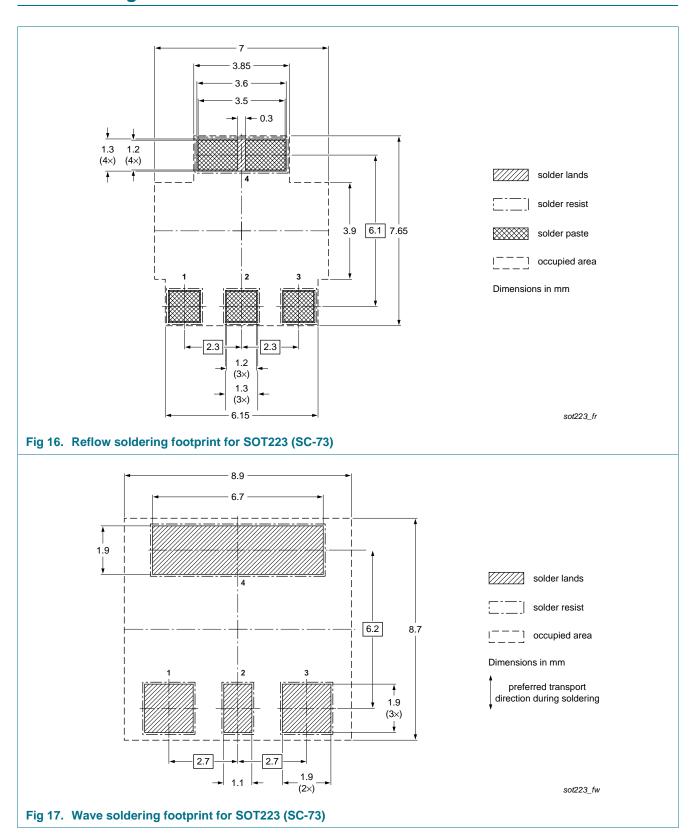


Fig 15. Package outline SOT223 (SC-73)

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10. Soldering



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11. Revision history

Table 8. Revision history

Release date	Data sheet status	Change notice	Supersedes
20110726	Product data sheet	-	PBSS306PZ v.2
In <u>7 "Characteristic</u><u>Fig 15.</u> updated	cs" new parameter added	l, I _{CES}	
20091211	Product data sheet	-	PBSS306PZ v.1
20060920	Product data sheet	-	-
	20110726 1.2 "Features and In 7 "Characteristic Fig 15. updated 12 "Legal informat 20091211	20110726 Product data sheet 1.2 "Features and benefits" updated In 7 "Characteristics" new parameter added Fig 15. updated 12 "Legal information" updated 20091211 Product data sheet	20110726 Product data sheet - 1.2 "Features and benefits" updated In 7 "Characteristics" new parameter added, I _{CES} Fig 15. updated 12 "Legal information" updated 20091211 Product data sheet -

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12. Legal information

12.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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